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May 1996
ADVANCE INFORMATION

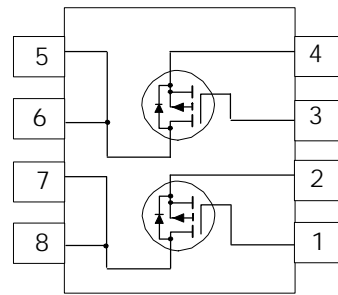
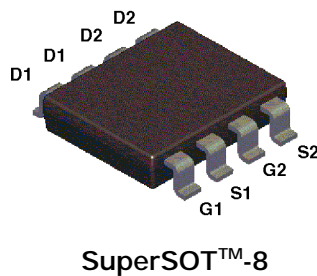
NDH8502P Dual P-Channel Enhancement Mode Field Effect Transistor

General Description

These P-Channel enhancement mode power field effect transistors are produced using National's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- -2.3A, -30V. $R_{DS(ON)} = 0.11\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} = 0.18\Omega @ V_{GS} = -4.5V$
- High density cell design for extremely low $R_{DS(ON)}$.
- Enhanced SuperSOT™-8 small outline surface mount package with high power and current handling capability.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	NDH8502P	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	-20	V
I_D	Drain Current - Continuous (Note 1)	-2.3	A
	- Pulsed	-7	
P_D	Maximum Power Dissipation (Note 1)	0.9	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	135	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	$^\circ\text{C/W}$